

## Smart Highside Power Switch

### Reversave™

- Reverse battery protection by self turn on of power MOSFET

### Features

- Short circuit protection
- Current limitation
- Overload protection
- Thermal shutdown
- Overvoltage protection (including load dump)
- Loss of ground protection
- Loss of  $V_{bb}$  protection (with external diode for charged inductive loads)
- Very low standby current
- Fast demagnetisation of inductive loads
- Electrostatic discharge (ESD) protection
- Optimized static electromagnetic compatibility (EMC)

### Product Summary

Operating voltage	$V_{bb(on)}$	5.0 ... 36	V
On-state resistance	$R_{ON}$	16	mΩ
Load current (ISO)	$I_L(ISO)$	25	A
Current limitation	$I_L(SCr)$	65	A

### Package

TO-252-5-1  
(DPAK 5 pin; less than half the size as TO 220 SMD)



### Diagnostic Function

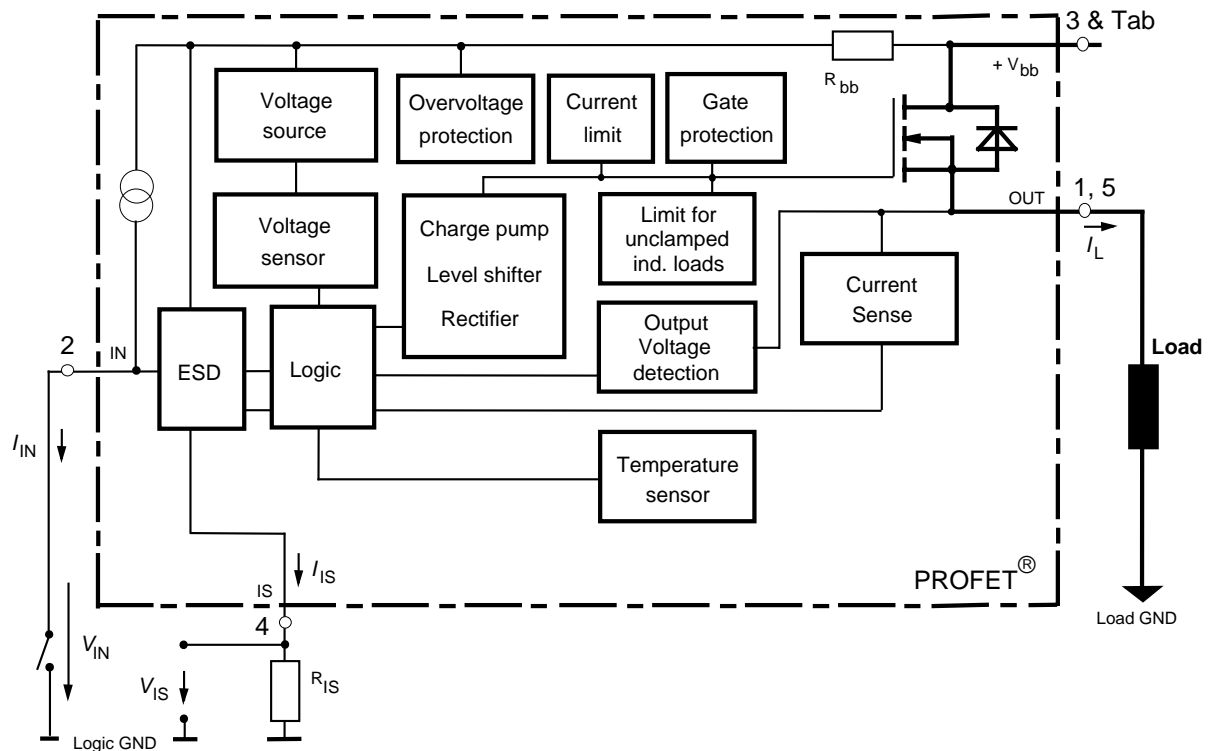
- Proportional load current sense (with defined fault signal while thermal shutdown)

### Application

- Power switch with current sense diagnostic feedback for 12V and 24 V DC grounded loads
- All types of resistive, capacitive and inductive loads (no PWM with inductive loads)
- Replaces electromechanical relays, fuses and discrete circuits

### General Description

N channel vertical power FET with charge pump, current controlled input and diagnostic feedback with load current sense, integrated in Smart SIPMOS® chip on chip technology. Fully protected by embedded protection functions.



Pin	Symbol	Function
1	OUT O	Output to the load. The pin 1 and 5 must be shorted with each other especially in high current applications!*)
2	IN I	Input, activates the power switch in case of short to ground
Tab/(3)	V <sub>bb</sub> +	Positive power supply voltage, the tab is shorted to this pin.
4	IS S	Diagnostic feedback providing a sense current proportional to the load current; high current on failure (see Truth Table)
5	OUT O	Output to the load. The pin 1 and 5 must be shorted with each other especially in high current applications!*)

\*) Not shorting all outputs will considerably increase the on-state resistance, reduce the peak current capability and decrease the current sense accuracy

**Maximum Ratings** at  $T_j = 25\text{ °C}$  unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 4)	$V_{bb}$	36	V
Supply voltage for full short circuit protection (see also diagram on page 9) $T_j = -40 \dots 150\text{ °C}$ :	$V_{bb}$	24 <sup>1)</sup>	V
Load dump protection $V_{LoadDump} = U_A + V_S$ , $U_A = 13.5\text{ V}$ $R_I = 2\ \Omega$ , $R_L = 2.7\ \Omega$ , $t_d = 200\text{ ms}$ , IN= low or high	$V_{Load\ dump}^{2)}$	60	V
Load current (Short-circuit current, see page 4)	$I_L$	self-limited	A
Operating temperature range	$T_j$	-40 ... +150	°C
Storage temperature range	$T_{stg}$	-55 ... +150	
Power dissipation (DC) $TC \leq 25\text{ °C}$	$P_{tot}$	42	W
Inductive load switch-off energy dissipation, single pulse $U=12\text{V}$ , $I=10\text{A}$ , $L=3\text{mH}$ $T_j=150\text{ °C}$ :	$E_{AS}$	0.15	J
Electrostatic discharge capability (ESD) (Human Body Model) acc. ESD assn. std. S5.1-1993; $R=1.5\text{k}\Omega$ ; $C=100\text{pF}$	$V_{ESD}$	4.0	kV
Current through input pin (DC)	$I_{IN}$	+15, -100	mA
Current through current sense pin (DC) see internal circuit diagrams page 7	$I_{IS}$	+15, -100	

1) Short circuit is tested with  $100\text{m}\Omega$  and  $20\mu\text{H}$

2)  $V_{Load\ dump}$  is set-up without the DUT connected to the generator per ISO 7637-1 and DIN 40839

## Thermal Characteristics

Parameter and Conditions	Symbol	Values			Unit
		min	typ	max	
Thermal resistance chip - case: junction - ambient (free air): SMD version, device on PCB <sup>4</sup> :	$R_{thJC}$ <sup>3)</sup>	--	--	1.5	K/W
	$R_{thJA}$	--	80	--	
				45	

## Electrical Characteristics

Parameter and Conditions at $T_j = -40^\circ\text{C} \dots 150^\circ\text{C}$ , $V_{bb} = 12\text{ V}$ unless otherwise specified	Symbol	Values			Unit
		min	typ	max	

## Load Switching Capabilities and Characteristics

On-state resistance (pin 3 to pin 1,5) $V_{IN} = 0$ , $I_L = 5\text{ A}$	$R_{ON}$	--	$T_j = 25^\circ\text{C}$ : 13	16	m $\Omega$
$T_j = 150^\circ\text{C}$ :			25	31	
Output voltage drop limitation at small load currents (Tab to pin 1,5) $T_j = -40 \dots 150^\circ\text{C}$ :	$V_{ON(NL)}$	--	50	--	mV
Nominal load current (Tab to pin 1,5) ISO Proposal: $V_{ON} = 0.5\text{ V}$ , $T_C = 85^\circ\text{C}$	$I_{L(ISO)}$	21	25	--	A
Turn-on time to 90% $V_{OUT}$ :	$t_{on}$	150	--	410	$\mu\text{s}$
Turn-off time to 10% $V_{OUT}$ :	$t_{off}$	70	--	410	
$R_L = 2,5\Omega$ , $T_j = -40 \dots 150^\circ\text{C}$					
Slew rate on 10 to 30% $V_{OUT}$ , $R_L = 2.5\ \Omega$ , $T_j = -40 \dots 150^\circ\text{C}$	$dV/dt_{on}$	0.1	--	1	V/ $\mu\text{s}$
Slew rate off 70 to 40% $V_{OUT}$ , $R_L = 2.5\ \Omega$ , $T_j = -40 \dots 150^\circ\text{C}$	$-dV/dt_{off}$	0.1	--	1	V/ $\mu\text{s}$

<sup>3)</sup> Thermal resistance  $R_{thCH}$  case to heatsink (about 0.5 ... 0.9 K/W with silicone paste) not included!

<sup>4)</sup> Device on 50mm\*50mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70 $\mu\text{m}$  thick) copper area for  $V_{bb}$  connection. PCB is vertical without blown air.

Parameter and Conditions at $T_j = -40^\circ\text{C} \dots 150^\circ\text{C}$ , $V_{bb} = 12\text{ V}$ unless otherwise specified	Symbol	Values			Unit
		min	typ	max	

### Operating Parameters

Operating voltage ( $V_{IN}=0$ )	$V_{bb(on)}$	5.0	--	36	V	
Undervoltage shutdown <sup>5)</sup>	$V_{bIN(u)}$	1.5	3.0	4.5	V	
Undervoltage restart of charge pump	$V_{bb(ucp)}$	3.0	4.5	6.0	V	
Overvoltage protection <sup>6)</sup> $I_{bb}=15\text{ mA}$	$V_{Z,IN}$	61	68	--	V	
Standby current $I_{IN}=0$	$T_j=-40\dots+25^\circ\text{C}$ : $T_j=150^\circ\text{C}$ :	$I_{bb(off)}$	-- --	2 4	5 8	$\mu\text{A}$

### Protection Functions

Short circuit current limit (Tab to pin 1,5) $V_{ON} = 12\text{V}$ , time until limitation max. $300\mu\text{s}$ $T_j = -40^\circ\text{C}$ : $T_j = 25^\circ\text{C}$ : $T_j = +150^\circ\text{C}$ :	$I_{L(SC)}$	35 35 35	75 65 65	110 110 125	A
Repetitive short circuit current limit, $T_j = T_{jt}$	$I_{L(SCr)}$	--	65	--	A
Output clamp (inductive load switch off) at $V_{OUT} = V_{bb} - V_{ON(CL)}$ (e.g. overvoltage) $I_L = 40\text{ mA}$ <sup>7)</sup>	$V_{ON(CL)}$	38	42	48	V
Thermal overload trip temperature	$T_{jt}$	150	--	--	$^\circ\text{C}$
Thermal hysteresis	$\Delta T_{jt}$	--	10	--	K

### Reverse Battery

Reverse battery voltage	$-V_{bb}$	--	--	20	V
On-state resistance (pin 1,5 to pin 3) $V_{bb} = -8\text{V}$ , $V_{IN} = 0$ , $I_L = -5\text{ A}$ , $R_{IS} = 1\text{ k}\Omega$ , $T_j = 25^\circ\text{C}$ : $V_{bb} = -12\text{V}$ , $V_{IN} = 0$ , $I_L = -5\text{ A}$ , $R_{IS} = 1\text{ k}\Omega$ , $T_j = 25^\circ\text{C}$ : $T_j = 150^\circ\text{C}$ :	$R_{ON(rev)}$	-- --	-- 16 25	22 19 32	$\text{m}\Omega$
Integrated resistor in $V_{bb}$ line	$R_{bb}$	--	200	--	$\Omega$

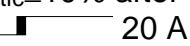
5)  $V_{bIN} = V_{bb} - V_{IN}$  see diagram page 11.

6) see also  $V_{ON(CL)}$  in circuit diagram page 7.

7) see also page 9

Parameter and Conditions at $T_j = -40^\circ\text{C} \dots 150^\circ\text{C}$ , $V_{bb} = 12\text{ V}$ unless otherwise specified	Symbol	Values			Unit
		min	typ	max	

**Diagnostic Characteristics**

Current sense ratio, static on-condition $k_{ILIS} = I_L : I_{IS}$ , $V_{ON} < 1.5\text{ V}^8)$ , $V_{IS} < V_{OUT} - 5\text{ V}$ , $V_{bIN} > 4.5\text{ V}$	$k_{ILIS}$	--	8200	--	
IL = 20A, $T_j = -40^\circ\text{C}$ :		7400	8300	9100	
$T_j = +25^\circ\text{C}$ :		7500	8300	9100	
$T_j = +150^\circ\text{C}$ :		7500	8200	8800	
IL = 5A, $T_j = -40^\circ\text{C}$ :		6800	8300	9700	
$T_j = +25^\circ\text{C}$ :		7200	8300	9300	
$T_j = +150^\circ\text{C}$ :		7200	8200	9000	
IL = 2.5A, $T_j = -40^\circ\text{C}$ :		6800	8500	10000	
$T_j = +25^\circ\text{C}$ :		6800	8500	9800	
$T_j = +150^\circ\text{C}$ :		6800	8100	9200	
IL = 1A, $T_j = -40^\circ\text{C}$ :		6800	8600	10500	
$T_j = +25^\circ\text{C}$ :		6800	8600	10500	
$T_j = +150^\circ\text{C}$ :		6800	8600	10500	
$I_{IN} = 0$ (e.g. during deenergising of inductive loads):		--	n.a.	--	
Sense current under fault conditions; $V_{DS} > 1.5\text{ V}$ , typ. $T_j = -40 \dots +150^\circ\text{C}$ :	$I_{IS, fault}$	2.5	4	--	mA
Fault-Sense signal delay after negative input slope	$t_{delay(fault)}$			0.8	ms
Current sense leakage current $I_{IN} = 0$ ; $V_{IN} = 0$ , $I_L = 0$ :	$I_{IS(LL)}$	--	--	0.5	$\mu\text{A}$
	$I_{IS(LH)}$	--	4	12	
Current sense settling time to $I_{IS\ static} \pm 10\%$ after positive input slope, $I_L = 0$  20 A, $T_j = -40 \dots +150^\circ\text{C}$ (not tested, specified by design)	$t_{son(IS)}$	--	--	400	$\mu\text{s}$
Overvoltage protection $I_{bb} = 15\text{ mA}$ $T_j = -40 \dots +150^\circ\text{C}$ :	$V_{bIS(Z)}$	61	68	--	V

**Input**

Required current capability of input switch $T_j = -40 \dots +150^\circ\text{C}$ :	$I_{IN(on)}$	--	0.7	1.2	mA
Maximum input current for turn-off $T_j = -40 \dots +150^\circ\text{C}$ :	$I_{IN(off)}$	--	--	50	$\mu\text{A}$

8) If  $V_{ON}$  is higher, the sense current is no longer proportional to the load current due to sense current saturation.

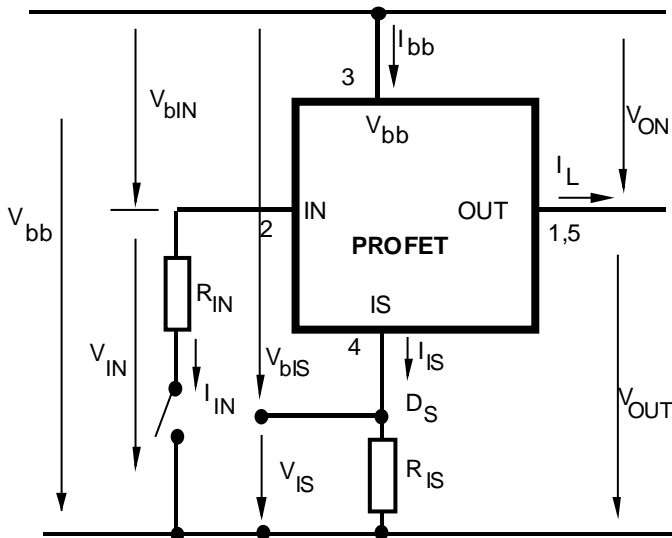
### Truth Table

	Input Current level	Output level	Current Sense $I_{IS}$
Normal operation	L	L	0
	H	H	nominal
Overload	L	L	0
	H	H	$I_{ISfault}$
Short circuit to GND	L	L	0
	H	L	$I_{ISfault}$
Overtemperature	L	L	0
	H	L	$I_{ISfault}$
Short circuit to $V_{bb}$	L	H	0
	H	H	<nominal <sup>9</sup>
Open load	L	Z	0
	H	H	0

L = "Low" Level  
H = "High" Level

Z = high impedance, potential depends on external circuit

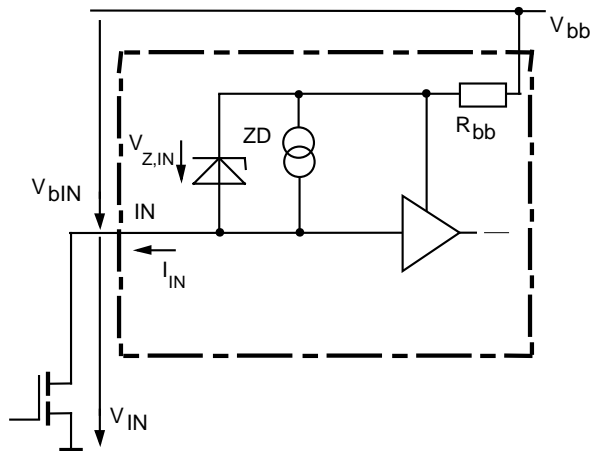
### Terms



Two or more devices can easily be connected in parallel to increase load current capability.

<sup>9)</sup> Low ohmic short to  $V_{bb}$  may reduce the output current  $I_L$  and therefore also the sense current  $I_{IS}$ .

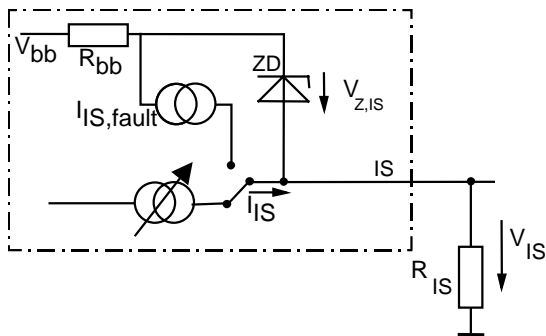
### Input circuit (ESD protection)



ESD-Zener diode: 68 V typ., max 15 mA;

### Current sense output

Normal operation

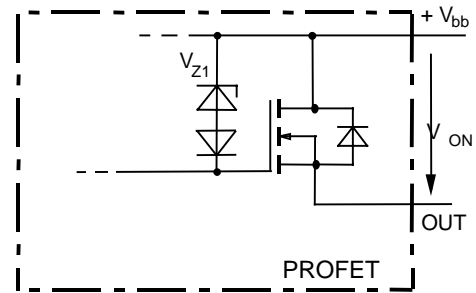


$V_{Z,IS} = 68\text{V}$  (typ.),  $R_{IS} = 1\text{ k}\Omega$  nominal (or  $1\text{ k}\Omega / n$ , if  $n$  devices are connected in parallel).  $I_{IS} = I_L / K_{ilis}$  can be only driven by the internal circuit as long as  $V_{out} - V_{IS} > 5\text{V}$ . If you want to measure load currents

up to  $I_{L(M)}$ ,  $R_{IS}$  should be less than  $\frac{V_{bb} - 5\text{V}}{I_{L(M)} / K_{ilis}}$ .

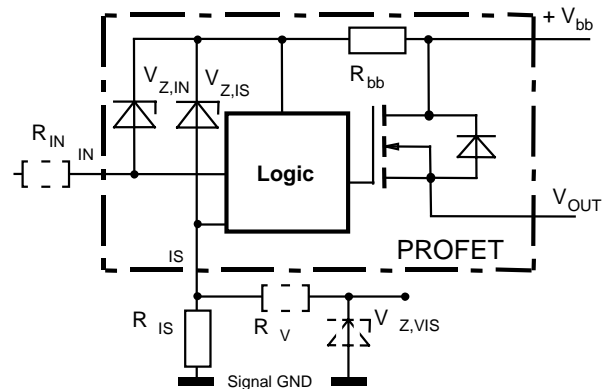
Note: For large values of  $R_{IS}$  the voltage  $V_{IS}$  can reach almost  $V_{bb}$ . See also overvoltage protection. If you don't use the current sense output in your application, you can leave it open.

### Inductive and overvoltage output clamp



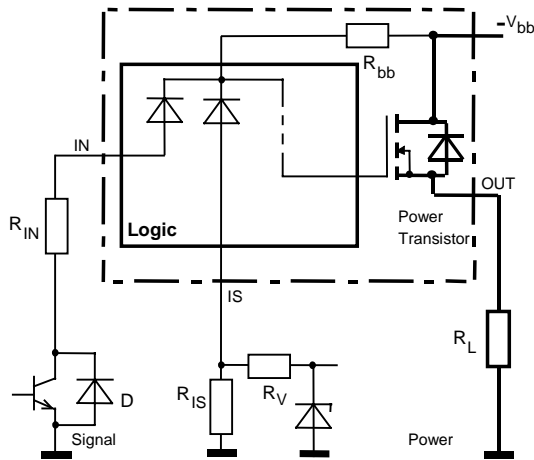
$V_{ON}$  is clamped to  $V_{ON(CI)} = 42\text{V}$  typ

### Overvoltage protection of logic part



$R_{bb} = 200\Omega$  typ.,  $V_{Z,IN} = V_{Z,IS} = 68\text{V}$  typ.,  $R_{IS} = 1\text{ k}\Omega$  nominal. Note that when overvoltage exceeds  $73\text{V}$  typ. a voltage above  $5\text{V}$  can occur between  $IS$  and  $GND$ , if  $R_V$ ,  $V_{Z,VIS}$  are not used.

**Reversave™ (Reverse battery protection)**



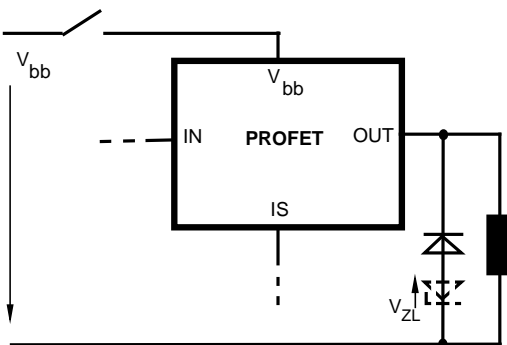
$R_V \geq 1k\Omega$ ,  $R_{IS} = 1k\Omega$  nominal. Add  $R_{IN}$  for reverse battery protection in applications with  $V_{bb}$  above 16V; recommended value:  $\frac{1}{R_{IN}} + \frac{1}{R_{IS}} + \frac{1}{R_V} = \frac{0.05A}{|V_{bb}|-12V}$

To minimise power dissipation at reverse battery operation, the summarised current into the IN and IS pin should be about 50mA. The current can be provided by using a small signal diode D in parallel to the input switch, by using a MOSFET input switch or by proper adjusting the current through  $R_{IS}$  and  $R_V$ .

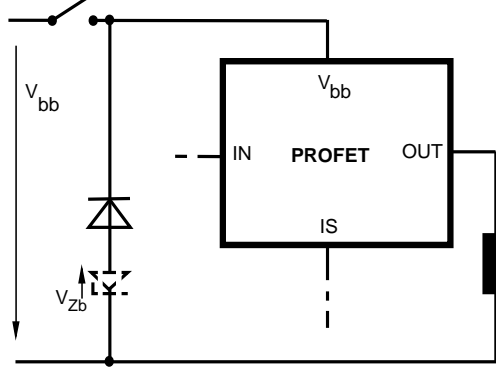
**V<sub>bb</sub> disconnect with energised inductive load**

Provide a current path with load current capability by using a diode, a Z-diode, or a varistor. ( $V_{ZL} < 73V$  or  $V_{Zb} < 30V$  if  $R_{IN}=0$ ). For higher clamp voltages currents at IN and IS have to be limited to 250 mA.

Version a:

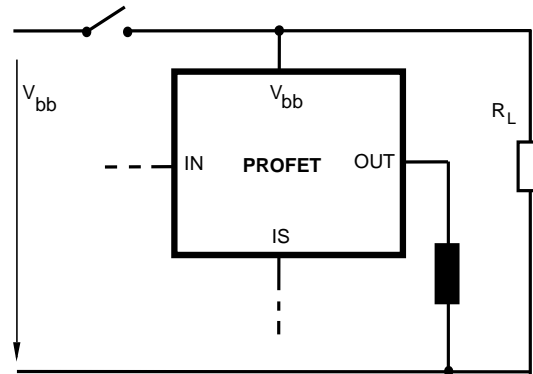


Version b:



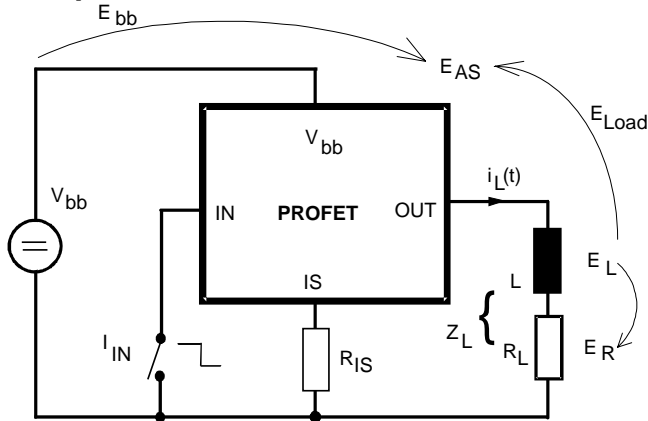
Note that there is no reverse battery protection when using a diode without additional Z-diode  $V_{ZL}$ ,  $V_{Zb}$ .

Version c: Sometimes a necessary voltage clamp is given by non inductive loads  $R_L$  connected to the same switch and eliminates the need of clamping circuit:





**Inductive load switch-off energy dissipation**



Energy stored in load inductance:

$$E_L = 1/2 \cdot L \cdot I_L^2$$

While demagnetising load inductance, the energy dissipated in PROFET is

$$E_{AS} = E_{bb} + E_L - E_R = \int V_{ON(CL)} \cdot i_L(t) dt,$$

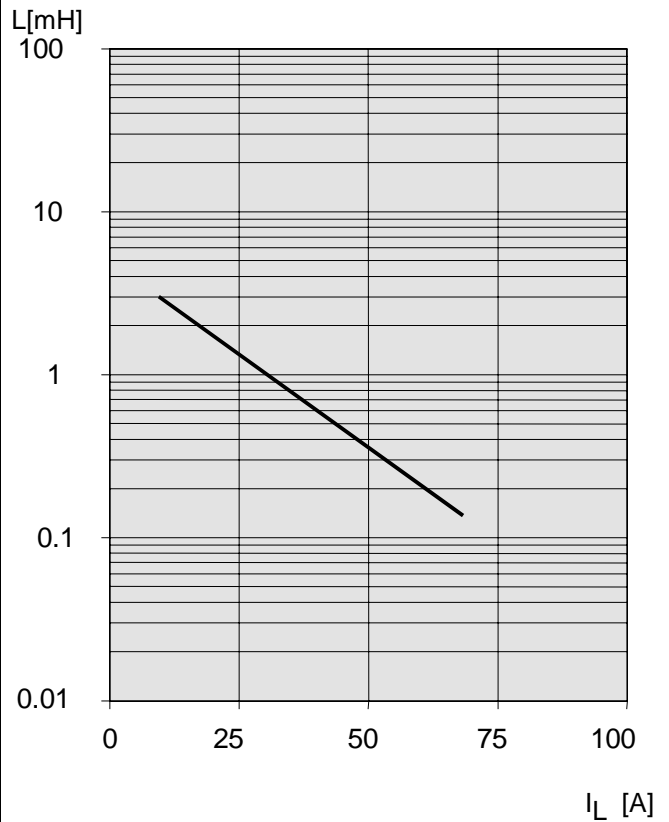
with an approximate solution for  $R_L > 0 \Omega$ :

$$E_{AS} = \frac{I_L \cdot L}{2 \cdot R_L} (V_{bb} + |V_{OUT(CL)}|) \ln \left( 1 + \frac{I_L \cdot R_L}{|V_{OUT(CL)}|} \right)$$

The device is not suitable for permanent PWM with inductive loads if active clamping occurs every cycle.

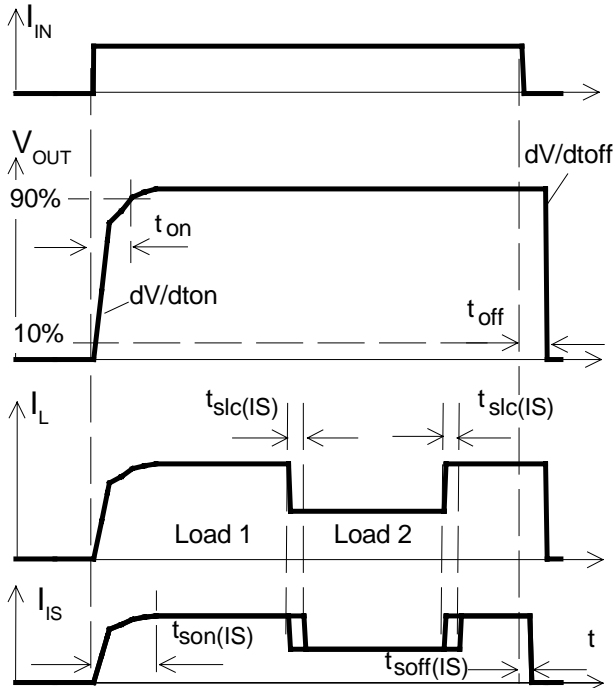
**Maximum allowable load inductance for a single switch off**

$L = f(I_L)$ ;  $T_{j,start} = 150^\circ C$ ,  $V_{bb} = 12 V$ ,  $R_L = 0 \Omega$



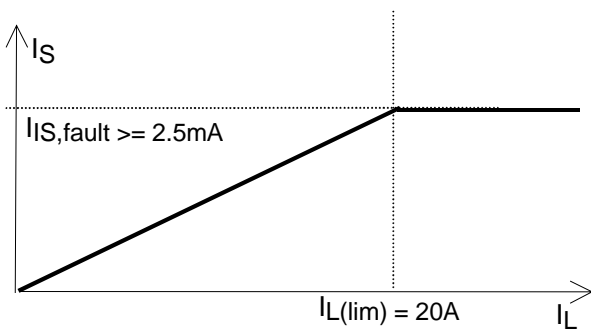
## Timing diagrams

**Figure 1a:** Switching a resistive load, change of load current in on-condition:

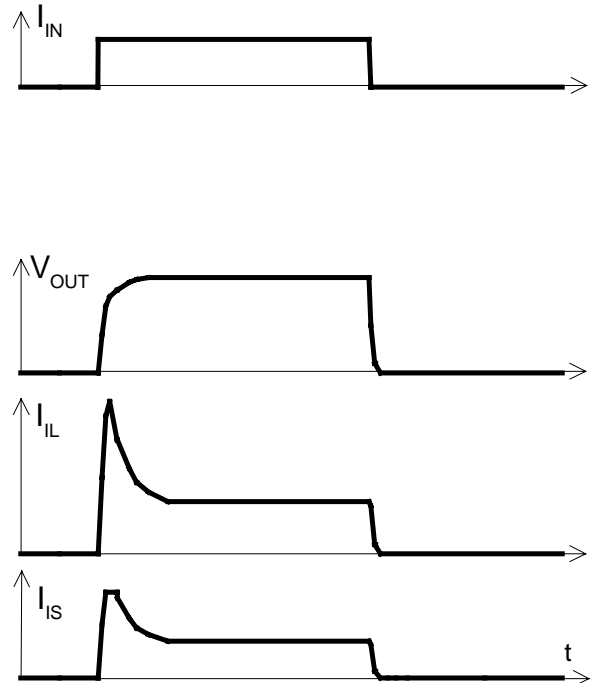


The sense signal is not valid during a settling time after turn-on/off and after change of load current.

**Figure 1b:** typical behaviour of sense output:

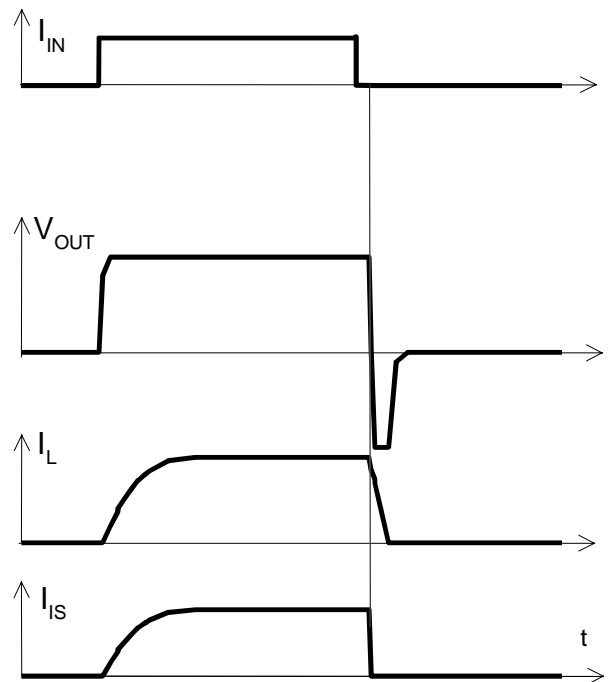


**Figure 2a:** Switching motors and lamps:

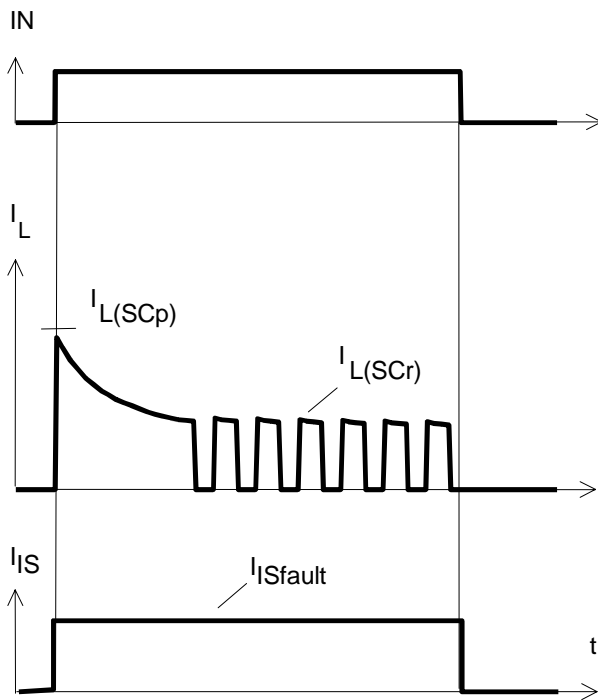


Sense current above  $I_{IS,fault}$  can occur at very high inrush currents.

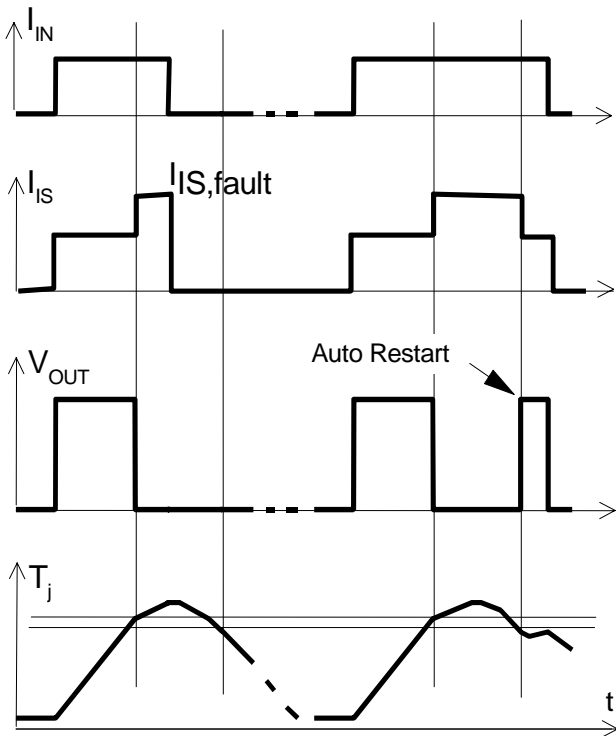
**Figure 2b:** Switching an inductive load:



**Figure 3a:** Short circuit:



**Figure 4a:** Overtemperature Reset if  $T_j < T_{jt}$



**Figure 5a:** Undervoltage restart of charge pump, overvoltage clamp

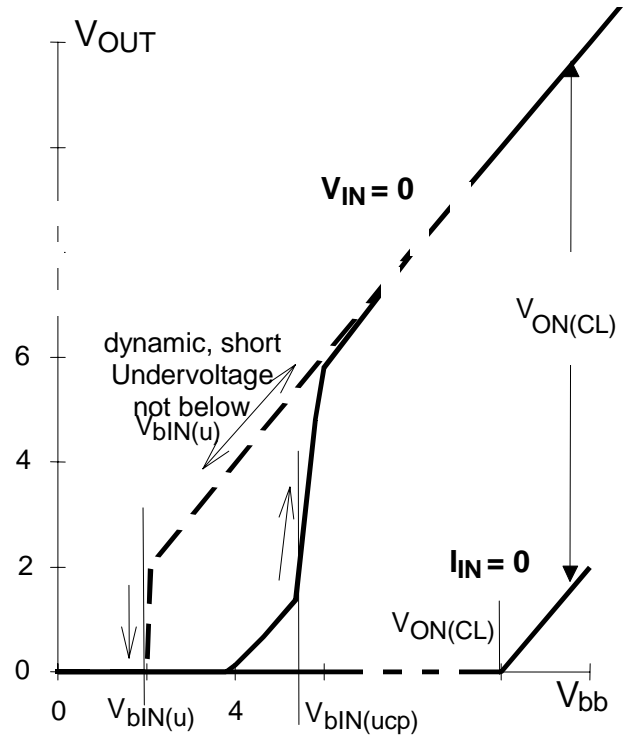


Figure 6a: Current sense versus load current:

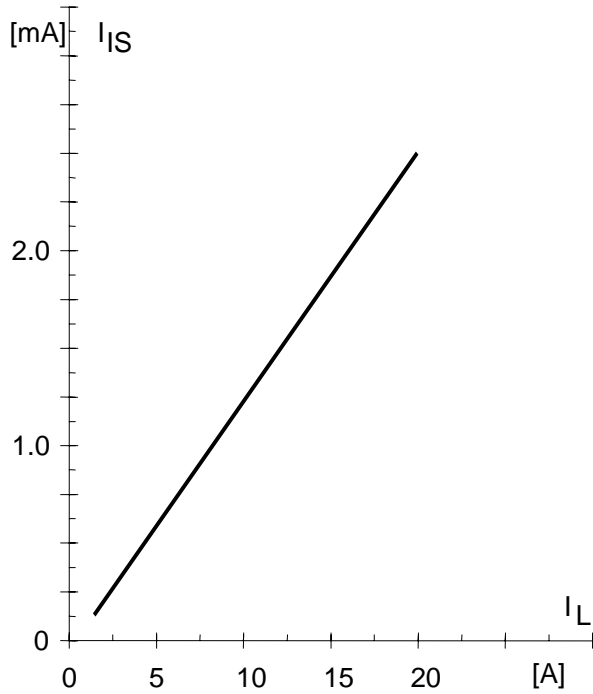


Figure 6b: Current sense ratio<sup>10</sup>:

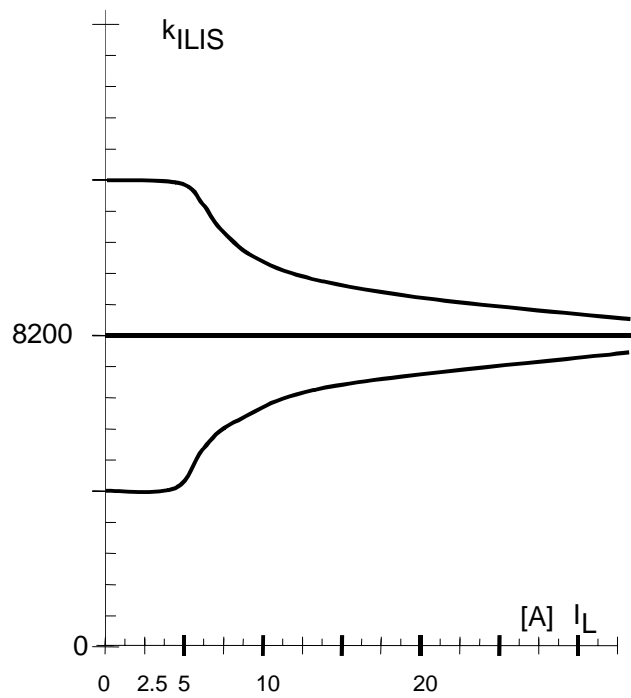
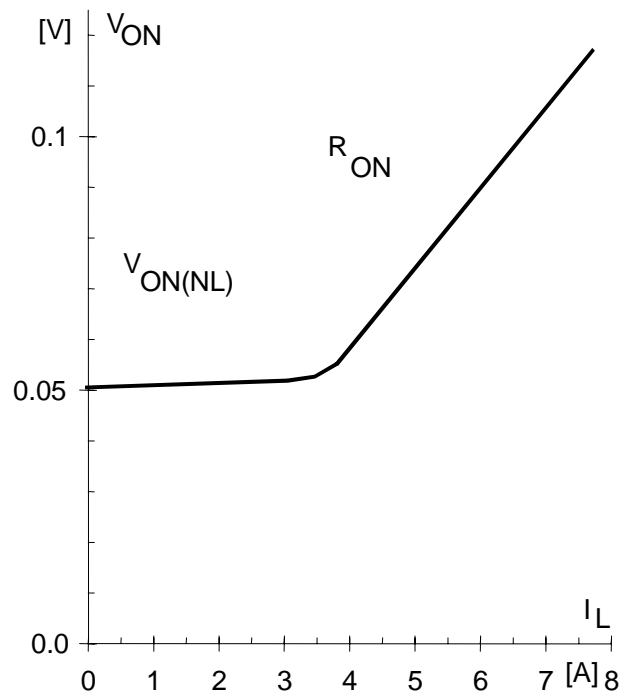


Figure 7a: Output voltage drop versus load current:



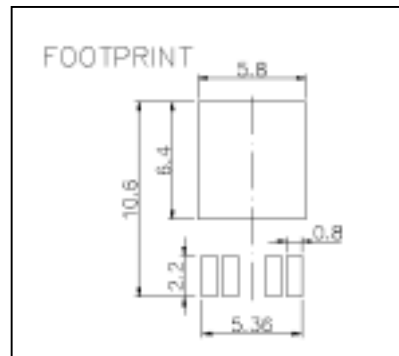
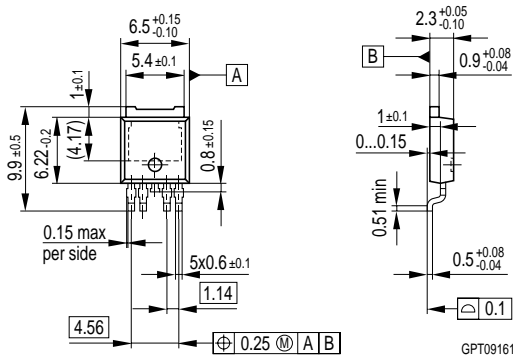
<sup>10)</sup> This range for the current sense ratio refers to all devices. The accuracy of the  $k_{ILIS}$  can be raised by means of calibration the value of  $k_{ILIS}$  for every single device.

## Package and Ordering Code

All dimensions in mm

### D-Pak-5 Pin: TO-252-5-1

Sales Code	BTS443P
Ordering code	Q67060-S7404-A 2



All metal surfaces tin plated, except area of cut.

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